



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
001/	30mΩ @ V _{GS} = 10V	5.5A
30V	42mΩ @ V _{GS} = 4.5V	4.7A

Features and Benefits

- 100% Unclamped Inductive Switching-Ensures More Reliable and Robust Application
- Low On-Resistance—Minimizes Power Losses
- Low Gate Charge—Minimizes Switching Losses
- Small Form Factor Low-Profile Package—Increased Power Density
- Sidewall Plated for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMN3032LFDBWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Description and Applications

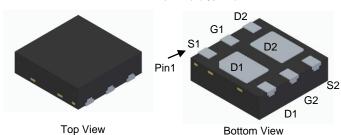
This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and ideal for use in:

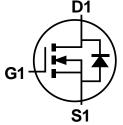
- **Body Control Electronics**
- **Power Management Functions**
- **DC-DC Converters**

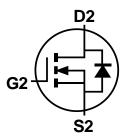
Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Terminals Connections: See Diagram Below
- Weight: 0.007 grams (Approximate)

U-DFN2020-6 (SWP) (Type B)







Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging		
DMN3032LFDBWQ-7	U-DFN2020-6 (SWP) (Type B)	3000/Tape & Reel		
DMN3032LFDBWQ-13	U-DFN2020-6 (SWP) (Type B)	10,000/Tape & Reel		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



NW = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020)M = Month (ex: 9 = September)

Date Code Key

Date Code Ney												
Year	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	G	Н	- 1	J	K	L	М	N	0	Р	R	S
Manth	lan	F-4	Man	A	Mari	lives	11	A	C	0-4	New	Dan
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	30	V
Gate-Source Voltage		Vgss	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	I _D	5.5 4.4	Α	
Maximum Continuous Body Diode Forward Currer	nt (Note 6)	Is	1.7	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1	%)	I _{DM}	30	А
Avalanche Current (Note 7) L = 0.1mH		las	12	Α
Avalanche Energy (Note 7) L = 0.1mH		Eas	7.7	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	0.82	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\Theta JA}$	153	°C/W
Total Power Dissipation (Note 6)		PD	1.37	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Rөja	91	°C/W
Thermal Resistance, Junction to Case (Note 6)		Rejc	30	C/VV
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

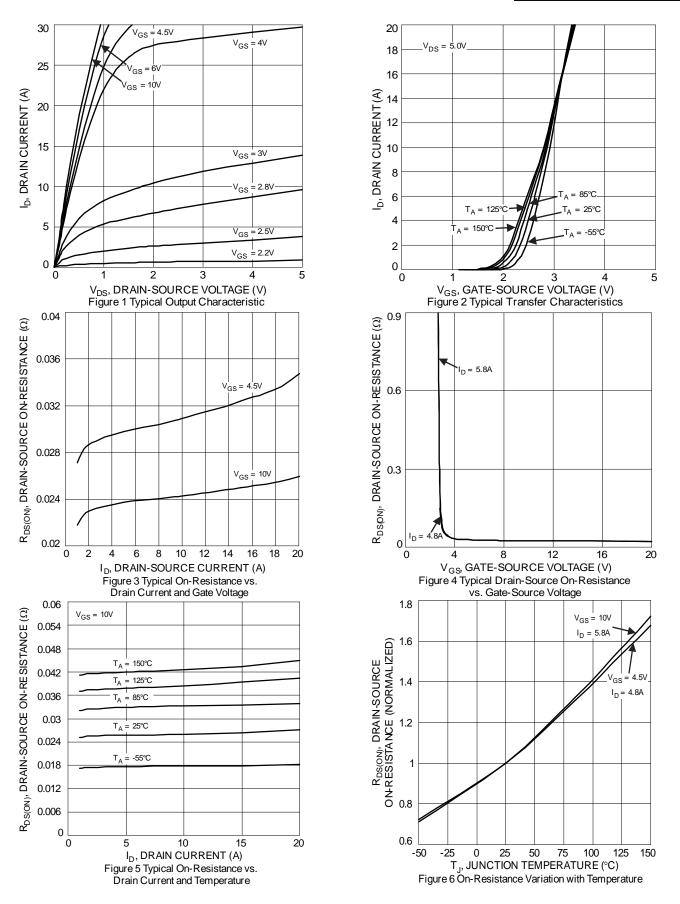
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)	Зуппоп	IVIIII	Тур	IVIAX	Ullit	Test Condition
Drain-Source Breakdown Voltage	BVpss	30	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	IDSS	_	_	1.0	μA	V _{DS} = 30V, V _{GS} = 0V
Zero Gate Voltage Drain Current T _J = +150°C (Note 9)	I _{DSS}	_	_	100	μA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	Igss	_	_	±100	nA	Vgs = ±20V, Vps = 0V
ON CHARACTERISTICS (Note 8)	1000	I	<u>I</u>	1	I	1100 ==01,120 01
Gate Threshold Voltage	Vgs(TH)	1.0	_	2.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Dunin Course On Begintages	_		24	30	0	V _{GS} = 10V, I _D = 5.8A
Static Drain-Source On-Resistance	RDS(ON)	_	30	42	mΩ	V _{GS} = 4.5V, I _D = 4.8A
Diode Forward Voltage	Vsp	_	0.7	1.2	V	V _G S = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 9)	•				l .	
Input Capacitance	Ciss	_	500	_	pF	
Output Capacitance	Coss	_	52	_	pF	V _{DS} = 15V, V _{GS} = 0V, - f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	44	_	pF	71 = 1.0WHZ
Gate Resistance	Rg	_	2.3	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (VGS = 4.5V)	Qg	_	5.0		nC	
Total Gate Charge (Vgs = 10V)	Qg	_	10.6	_	nC	15)/ 1 5 0 4
Gate-Source Charge	Q _{gs}	_	1.3	_	nC	$V_{DS} = 15V, I_{D} = 5.8A$
Gate-Drain Charge	Q _{gd}	_	1.8	_	nC	
Turn-On Delay Time	tD(ON)	_	2.2	_	ns	
Turn-On Rise Time	t _R	_	2.6	_	ns	V _{DD} = 15V, V _{GS} = 10V,
Turn-Off Delay Time	tD(OFF)	_	9.7	_	ns	$R_L = 2.6\Omega$, $R_G = 3\Omega$
Turn-Off Fall Time	tF	_	2.0	_	ns	

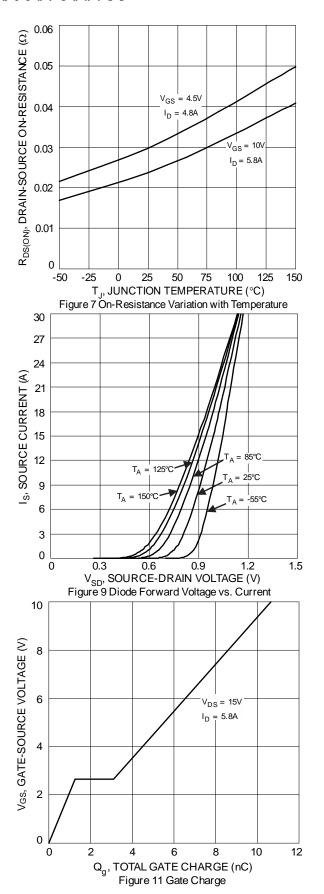
Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
- 7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.









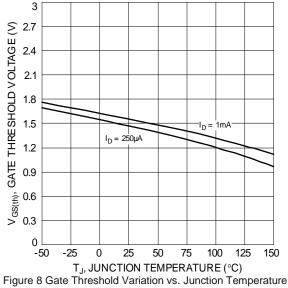
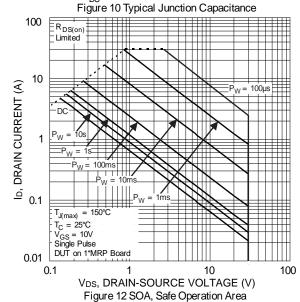


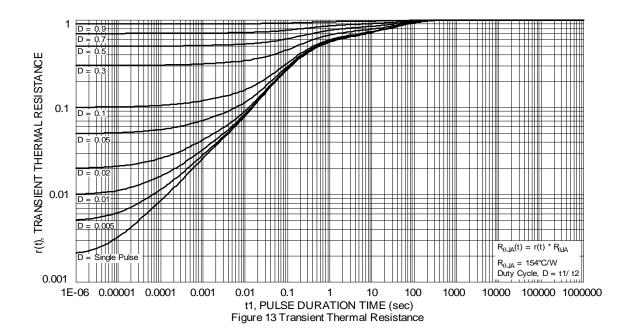
Figure 8 Gate Threshold Variation vs. Junction Temperature

1000

Coss





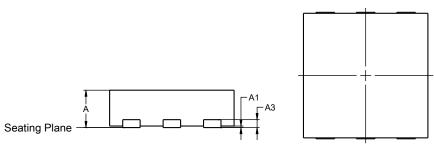


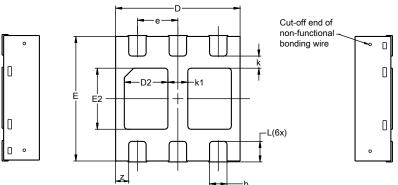


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (SWP) (Type B)



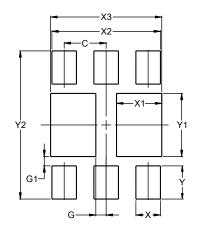


U-DFN2020-6 (SWP) (Type B)							
Dim	Min Max Typ						
Α	0.55	0.65	0.60				
A1	0.00	0.05	0.03				
А3			0.127				
b	0.23	0.33	0.28				
D	1.95	2.05	2.00				
D2	0.60	0.80	0.70				
Е	1.95	2.05	2.00				
E2	0.88	1.08	0.98				
е	0.65BSC						
k	0.195BSC						
k1	0.32BSC						
٦	0.28	0.38	0.33				
Z	0.21BSC						
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (SWP) (Type B)



Dimensions	Value
	(in mm)
С	0.650
G	0.160
G1	0.145
Х	0.380
X1	0.700
X2	1.680
Х3	1.720
Y	0.515
Y1	0.980
Y2	2.300



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